

1 **ABSTRACT OF THE DISCLOSURE**

2 In one aspect, the invention includes a semiconductor processing
3 method. An antireflective material layer is formed over a substrate.
4 At least a portion of the antireflective material layer is annealed at a
5 temperature of greater than about 400° C. A layer of photoresist is
6 formed over the annealed antireflective material layer. The layer of
7 photoresist is patterned. A portion of the antireflective material layer
8 unmasked by the patterned layer of photoresist is removed. In another
9 aspect, the invention includes the following semiconductor processing.
10 An antireflective material layer is formed over a substrate. The
11 antireflective material layer is annealed at a temperature of greater than
12 about 400° C. A layer of photoresist is formed over the annealed
13 antireflective material layer. Portions of the layer of photoresist are
14 exposed to radiation waves. Some of the radiation waves are absorbed
15 by the antireflective material during the exposing.

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